DFN1006-2L ESD 静电保护二极管

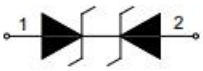
■Features 特点

IEC 61000-4-2 Level 4 ESD Protection 静电保护
- ±8kV Contact Discharge 接触放电
- ±15kV Air Discharge 空气放电

■Applications 应用

Communication systems 通讯系统
Portable electronics 便携式电子产品
Notebooks & Handhelds 笔记本或手持机
Cellular handsets and accessories 蜂窝手机及附件

■Internal Schematic Diagram 内部结构



DFN1006-2L

■Absolute Maximum Ratings 最大额定值

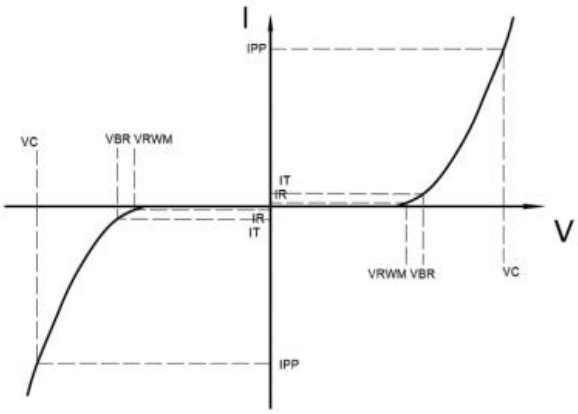
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
ESD (IEC61000-4-2 contact discharge) @25℃接触放电	V_{ESD}	±8	KV
ESD (IEC61000-4-2 air discharge) @25℃ 空气放电	V_{ESD}	±15	KV
Peak Pulse Current @25℃峰值脉冲电流	I_{PP}	4	A
Peak Pulse Power @25℃峰值脉冲功率	P_{PK}	272	W
Lead Temperature 管脚温度	T_L	260	℃
Operating Temperature 工作温度	T_{op}	-40~125	℃
Junction Temperature 结温	T_J	150	℃
Storage Temperature 储存温度	T_{stg}	-55~150	℃

■Electrical Characteristics 电特性

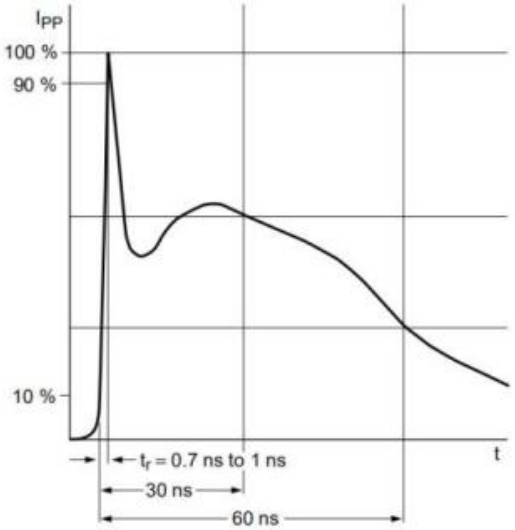
(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃)

Characteristic Parameters 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Reverse Stand-off Voltage 反向工作电压	V_{RWM}			36	V	
Reverse Breakdown Voltage 反向击穿电压	V_{BR}	39		45	V	I_T=1mA
Reverse Leakage Current 反向漏电流	I_R			0.1	μA	V_{RWM}=36V
Clamping Voltage 钳位电压	V_C		50	52	V	I_{PP}=1A,tp=8/20μs
Clamping Voltage 钳位电压	V_C		66	68	V	I_{PP}=4A,tp=8/20μs
Diode Capacitance 二极管电容	C_D		6	7	pF	V_R=0V,f=1MHz

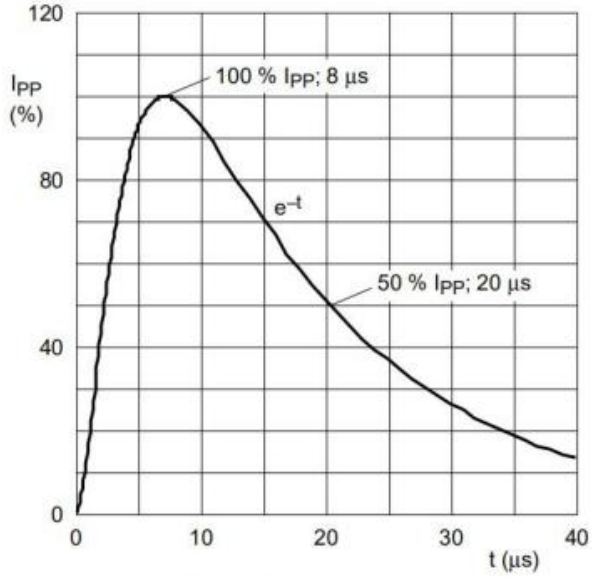
Symbol	Parameters
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
I_F	Forward Current
V_F	Forward Voltage @ I_F



■Typical Characteristic Curve 典型特性曲线

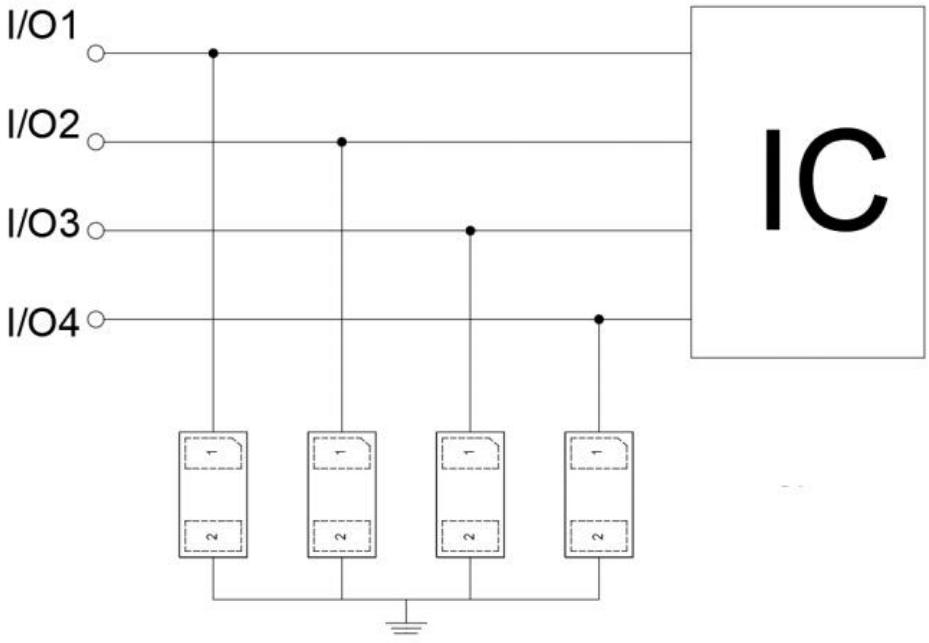


IEC61000-4-2 Waveform

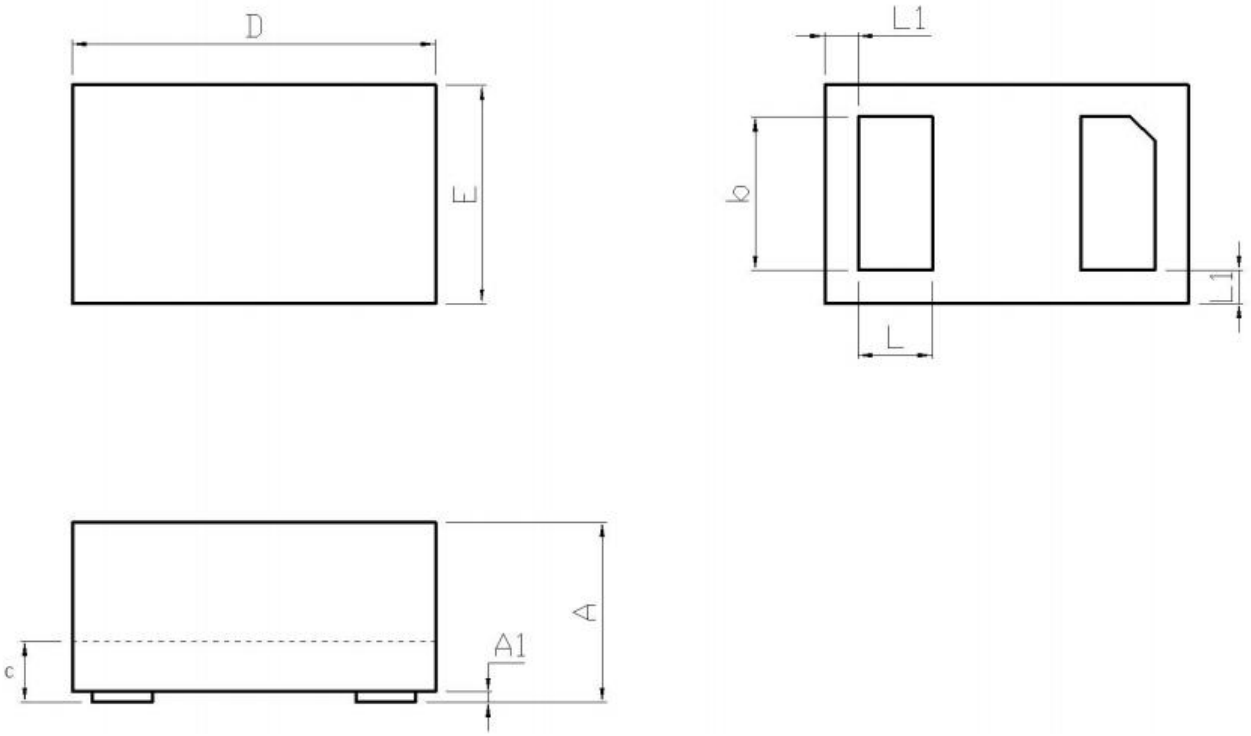


IEC 61000-4-5 Waveform(8/20µs pulse)

■Typical Applications 典型应用



■ Dimension 外形封装尺寸



DFN1006-2L (mm)			
Dim	Min	Typ.	Max
A	0.46	0.48	0.50
A1	0	0.02	0.05
b	0.45	0.5	0.55
c	0.1	0.12	0.14
D	0.95	1.00	1.05
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.035	0.05	0.065
h	0.07	0.12	0.17